FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTORNEY DOCKET NO. 005552.USA/AMT	SERIAL NO. N/A
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	APPLICANT: Yu, et al	
	FILING DATE: Herewith	GROUP: ~~Unknown~~ 2823

U.S. PATENT DOCUMENTS

Examiner Initial		DOCKET NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Lee	AA	4 7 3 2 7 6 1	03/22/88	Machida, et al.	204	192.32	
	AB	4 9 6 2 0 6 3	10/09/90	Maydan, et al.	437	228	
	AC	5 0 8 9 4 4 2	02/18/92	Olmer	204	192.3	
	AD	5 1 2 4 0 1 4	06/23/92	Foo, et al.	204	192.32	
	AE	5 2 0 4 2 8 8	04/20/93	Marks, et al.	437	228	
Lee	AF	5 2 4 4 8 4 1	09/14/93	Marks, et al.	437	228	
	AG						
	AH						
	AI						
	AJ						
	AK						

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FOREIGN PATENT DOCUMENTS

		DOCKET NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
Lee	AL	0 5 2 0 5 1 9	12/30/92	EP			X	
	AM							
	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

Lee	AQ	Kuo, Y., "Etch Mechanisim in the Low Refractive Index Silicon Nitride Plasma-enhanced Chemical Vapor Deposition Process." Applied Physics Letters, 63(2): 144-146 (1993)
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Lee	AS	Li, J., et al., "Modeling Studies of the Mechanisms in Biased ECR CVD"
Lee	AT	Lassig, S., et al., "Intermetal Dielectric Deposition by Electron Cyclotron Resonance Chemical Vapor Deposition (ECR CVD)," pp. 1-21

EXAMINER: Kevin Mary Lee DATE CONSIDERED: 7/17/2002

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.